

Electronic Supplementary Information for:

Low Voltage Electrolyte-Gated Organic Transistors Making Use of High Surface Area Activated Carbon Gate Electrodes

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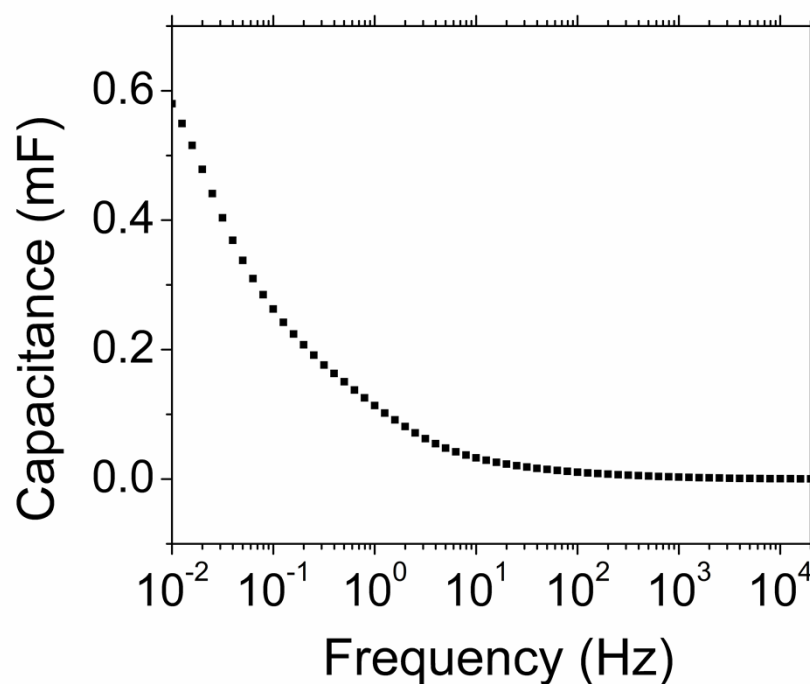


Fig. S1 Frequency dependence of the capacitance of the MEH-PPV working electrode at 0.8 V vs activated carbon (small sized) quasi reference electrode with activated carbon gate as the counter electrode.

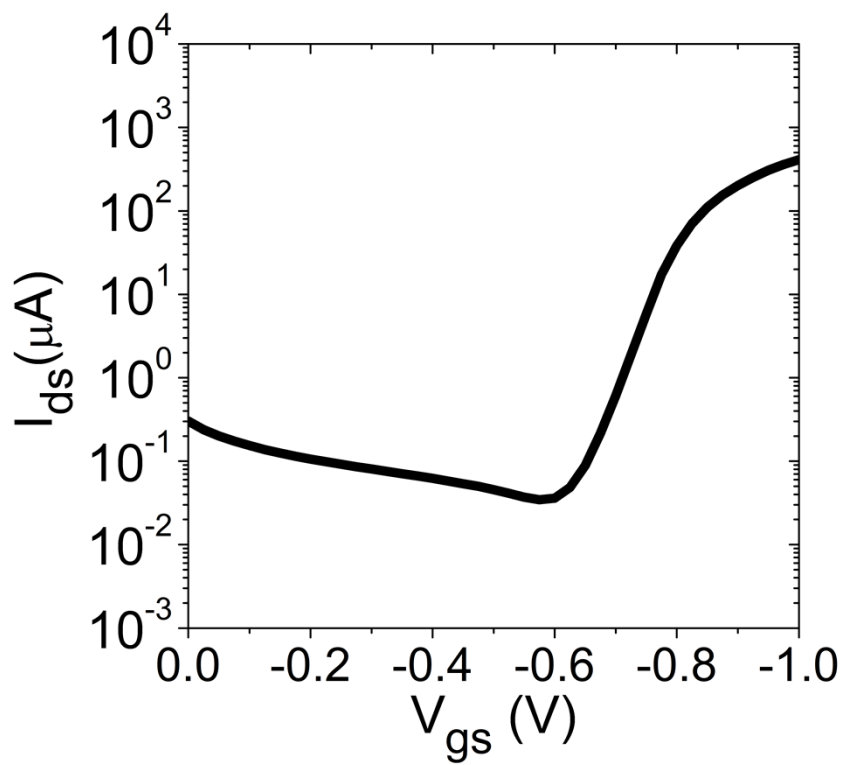


Fig. S2 Transfer characteristics in the saturation regime ($V_{ds} = -0.3$ V) for [EMIM][TFSI]-gated MEH-PPV transistors, sweep rate $50 \text{ mV} \cdot \text{s}^{-1}$.

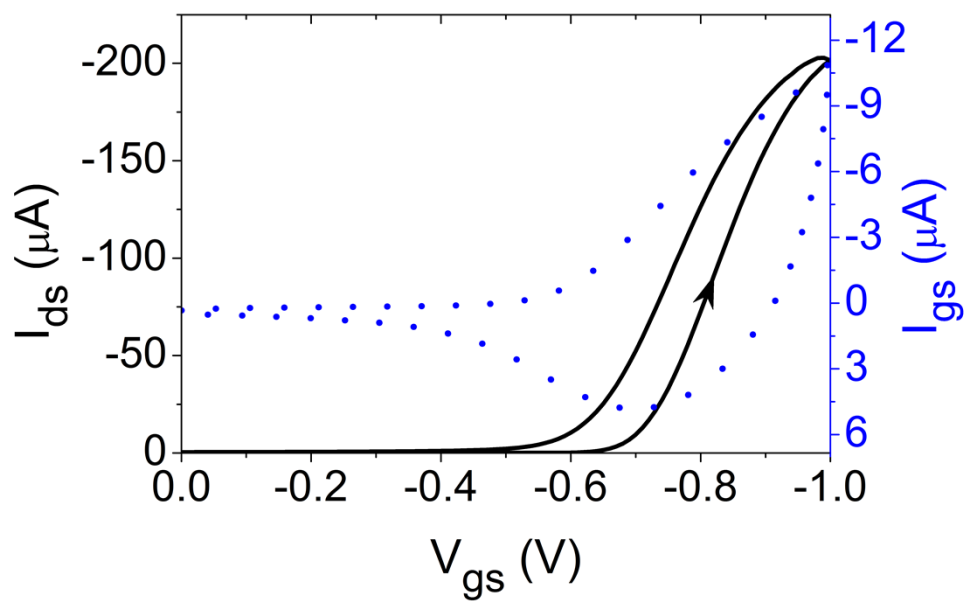


Fig. S3 [EMIM][TFSI]-gated MEH-PPV transistor transfer characteristics in the linear regime ($V_{ds} = -0.1$ V). I_{ds} (left axis, solid black line) and I_{gs} (right axis, dotted blue line) are plotted vs V_{gs} , sweep rate $10 \text{ mV} \cdot \text{s}^{-1}$.